NSN 5961-01-120-1235

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View Online at https://aerobasegroup.com/nsn/5961-01-120-1235
Inclosure Material:
Metal
Overall Length:
Between 0.250 inches and 0.450 inches
Overall Diameter:
0.875 inches
End Application:
F16maintntring 81755 fscm
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-3
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
80.0 collector to base voltage/static/emitter open and 80.0 collector to emitter voltage/static/base open and 5.0 emitter to base voltage,
static, collector open
Current Rating Per Characteristic:
Between 0.25 amperes source cutoff current and 10.00 amperes source cutoff current
Power Rating Per Characteristic:
6.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: npn
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
1 case and 2 pin
Specification Data:
81349-mil-s-19500/523 government specification
Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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